Bernd Rauschenbach

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Temperature dependent evolution of local structure in chalcogenide-based superlattices. Applied Surface Science, 2021, 536, 147959.	6.1	42
2	Epitaxial layered Sb ₂ Te ₃ thin films for memory and neuromorphic applications. 2D Materials, 2021, 8, 045027.	4.4	14
3	Structural Transitions in Ge2Sb2Te5 Phase Change Memory Thin Films Induced by Nanosecond UV Optical Pulses. Materials, 2020, 13, 2082.	2.9	13
4	Biaxially Textured Titanium Thin Films by Oblique Angle Deposition: Conditions and Growth Mechanisms. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900636.	1.8	4
5	Impact of interfaces on bipolar resistive switching behavior in amorphous Ge–Sb–Te thin films. Journal Physics D: Applied Physics, 2020, 53, 184002. Strain-induced phase selection in epitaxial <mml:math< td=""><td>2.8</td><td>13</td></mml:math<>	2.8	13
6	xmlns:mml="http://www.w3.org/1998/Math/MathML"> <mml:mrow> <mml:mi mathvariant="normal">G <mml:msub> <mml:mi mathvariant="normal">e <mml:mn>2 </mml:mn> </mml:mi </mml:msub> <mml:mi mathvariant="normal">S <mml:msub> <mml:mi< td=""><td>2.4</td><td>3</td></mml:mi<></mml:msub></mml:mi </mml:mi </mml:mrow>	2.4	3
7	mathvariant="normal">b <mml:mn>2</mml:mn> <mml:mi mathvariant="normal" Difect Measurement of Crystal Growth Velocity in Epitaxial Phase-Change Material Thin Films. ACS Applied Materials & Interfaces, 2019, 11, 41544-41550.</mml:mi 	8.0	13
8	Influence of nitrogen ion species on mass-selected low energy ion-assisted growth of epitaxial GaN thin films. Applied Surface Science, 2019, 498, 143830.	6.1	1
9	<i>In situ</i> observations of the reversible vacancy ordering process in van der Waals-bonded Ge–Sb–Te thin films and GeTe–Sb ₂ Te ₃ superlattices. Nanoscale, 2019, 11, 10838-10845.	5.6	43
10	Au and Ag films and nanostructures for detection of fungicide mancozeb: SERS analyses. , 2019, , .		9
11	Atomic-scale observation of defects motion in van der Waals layered chalcogenide based materials. Scripta Materialia, 2019, 166, 154-158.	5.2	17
12	Influence of substrate dimensionality on the growth mode of epitaxial 3D-bonded GeTe thin films: From 3D to 2D growth. Materials and Design, 2019, 168, 107657.	7.0	18
13	Phase change thin films for non-volatile memory applications. Nanoscale Advances, 2019, 1, 3836-3857.	4.6	97
14	Crystalline Ti-nanostructures prepared by oblique angle deposition at room temperature. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2018, 36, .	1.2	4
15	Van der Waals interfacial bonding and intermixing in GeTe-Sb2Te3-based superlattices. Nano Research, 2018, 11, 1676-1686.	10.4	62
16	SERS analyses of thiamethoxam assisted by Ag films and nanostructures produced by laser techniques. Journal of Raman Spectroscopy, 2018, 49, 397-403.	2.5	15
17	Ultrafast interfacial transformation from 2D- to 3D-bonded structures in layered Ge–Sb–Te thin films and heterostructures. Nanoscale, 2018, 10, 22946-22953.	5.6	36
18	Glancing Angle Deposition for Biosensing Applications. , 2018, , 129-137.		2

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19	Comparative study of sculptured metallic thin films deposited by oblique angle deposition at different temperatures. Beilstein Journal of Nanotechnology, 2018, 9, 954-962.	2.8	15
20	Impact of disorder on optical reflectivity contrast of epitaxial Ge ₂ Sb ₂ Te ₅ thin films. CrystEngComm, 2018, 20, 3688-3695.	2.6	22
21	Realization of Multilevel States in Phaseâ€Change Thin Films by Fast Laser Pulse Irradiation. Advanced Optical Materials, 2017, 5, 1700169.	7.3	43
22	Graphene on silicon dioxide via carbon ion implantation in copper with PMMA-free transfer. Applied Physics Letters, 2017, 110, .	3.3	4
23	Research Update: Van-der-Waals epitaxy of layered chalcogenide Sb ₂ Te ₃ thin films grown by pulsed laser deposition. APL Materials, 2017, 5, 050701.	5.1	37
24	Glancing angle deposition of sculptured thin metal films at room temperature. Nanotechnology, 2017, 28, 385604.	2.6	23
25	Topography evolution of germanium thin films synthesized by pulsed laser deposition. AIP Advances, 2017, 7, .	1.3	5
26	Atomic structure and dynamic reconfiguration of layered defects in van der Waals layered Ge-Sb-Te based materials. Acta Materialia, 2017, 141, 92-96.	7.9	59
27	Ion mass and energy selective hyperthermal ion-beam assisted deposition setup. Review of Scientific Instruments, 2017, 88, 063306.	1.3	5
28	Epitaxial formation of cubic and trigonal Ge-Sb-Te thin films with heterogeneous vacancy structures. Materials and Design, 2017, 115, 138-146.	7.0	36
29	Enhanced intrinsic fluorescence from carboxidized nano-sculptured thin films of silver and their application for label free dual detection of glycated hemoglobin. Optics Express, 2017, 25, 4761.	3.4	14
30	Ion Beam Assisted Deposition of Thin Epitaxial GaN Films. Materials, 2017, 10, 690.	2.9	8
31	Microstructure evolution in pulsed laser deposited epitaxial Ge-Sb-Te chalcogenide thin films. Journal of Alloys and Compounds, 2016, 676, 582-590.	5.5	32
32	Epitaxial Ge2Sb2Te5 films on Si(111) prepared by pulsed laser deposition. Thin Solid Films, 2016, 619, 81-85.	1.8	14
33	Local atomic arrangements and lattice distortions in layered Ge-Sb-Te crystal structures. Scientific Reports, 2016, 6, 26724.	3.3	42
34	Crystallization of Ge2Sb2Te5 thin films by nano- and femtosecond single laser pulse irradiation. Scientific Reports, 2016, 6, 28246.	3.3	68
35	Real-space imaging of atomic arrangement and vacancy layers ordering in laser crystallised Ge2Sb2Te5 phase change thin films. Acta Materialia, 2016, 105, 1-8.	7.9	84
36	Embedded Ge nanocrystals in SiO2 synthesized by ion implantation. Journal of Applied Physics, 2015, 118,	2.5	12

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37	Focused high- and low-energy ion milling for TEM specimen preparation. Microelectronics Reliability, 2015, 55, 2119-2125.	1.7	51
38	Highly sensitive and specific detection of E. coli by a SERS nanobiosensor chip utilizing metallic nanosculptured thin films. Analyst, The, 2015, 140, 3201-3209.	3.5	80
39	An aberration-corrected STEM study of structural defects in epitaxial GaN thin films grown by ion beam assisted MBE. Micron, 2015, 73, 1-8.	2.2	18
40	Low temperature epitaxy of Ge-Sb-Te films on BaF2 (111) by pulsed laser deposition. Applied Physics Letters, 2014, 105, 221908.	3.3	21
41	Direct imaging of light elements by annular dark-field aberration-corrected scanning transmission electron microscopy. Applied Physics Letters, 2014, 104, 071908.	3.3	14
42	Epitaxial growth of Ge-Sb-Te films on KCl by high deposition rate pulsed laser deposition. Journal of Applied Physics, 2014, 115, 213504.	2.5	12
43	Direct imaging of crystal structure and defects in metastable Ge2Sb2Te5 by quantitative aberration-corrected scanning transmission electron microscopy. Applied Physics Letters, 2014, 104, .	3.3	51
44	High-fluence hyperthermal ion irradiation of gallium nitride surfaces at elevated temperatures. Applied Surface Science, 2014, 317, 811-817.	6.1	6
45	SERS Biosensor Using Metallic Nanoâ€Sculptured Thin Films for the Detection of Endocrine Disrupting Compound Biomarker Vitellogenin. Small, 2014, 10, 3579-3587.	10.0	78
46	Detailed study of surface-enhanced Raman scattering from metallic nanosculptured thin films and their potential for biosensing. Journal of Nanophotonics, 2012, 6, 061605-1.	1.0	24
47	Back Cover: Nonâ€periodic nanoscale templates by diffraction mask projection laser ablation (Phys.) Tj ETQq1 1	0.784314 1.8	rgBT /Overlo
48	Effects of annealing on arrays of Ge nanocolumns formed by glancing angle deposition. Applied Surface Science, 2012, 258, 9762-9769.	6.1	8
49	Nonâ€periodic nanoscale templates by diffraction mask projection laser ablation. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 2208-2211.	1.8	1
50	Epitaxial GaN films by hyperthermal ion-beam nitridation of Ga droplets. Journal of Applied Physics, 2012, 111, 113521.	2.5	14
51	Initial stages of the ion-beam assisted epitaxial GaN film growth on 6H-SiC(0001). Thin Solid Films, 2012, 520, 3936-3945.	1.8	18
52	Growth temperature altered morphology of Ge nanocolumns. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 851-856.	1.8	13
53	Glancing angle deposition of Ge nanorod arrays on Si patterned substrates. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2011, 29, .	2.1	11
54	Optimized growth of Ge nanorod arrays on Si patterns. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2011, 29, 051501.	2.1	13

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55	Dünne Schichten durch Deposition unter streifenden Einfall. Vakuum in Forschung Und Praxis, 2010, 22, 14-19.	0.1	2
56	Nanostructures by diffraction mask projection laser ablation. Physica Status Solidi (B): Basic Research, 2010, 247, 1372-1383.	1.5	12
57	Arbitrarily shaped Si nanostructures by glancing angle ion beam sputter deposition. Physica Status Solidi (B): Basic Research, 2010, 247, 1310-1321.	1.5	23
58	Periodically arranged Si nanostructures by glancing angle deposition on patterned substrates. Physica Status Solidi (B): Basic Research, 2010, 247, 1322-1334.	1.5	29
59	Tubular magnetic nanostructures based on glancing angle deposited templates and atomic layer deposition. Physica Status Solidi (B): Basic Research, 2010, 247, 1365-1371.	1.5	25
60	Gold nanostructure matrices by diffraction mask-projection laser ablation: extension to previously inaccessible substrates. Nanotechnology, 2010, 21, 175304.	2.6	9
61	Influence of substrate temperature on glancing angle deposited Ag nanorods. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2010, 28, 1002-1009.	2.1	30
62	Plasmonic Activity of Large-Area Gold Nanodot Arrays on Arbitrary Substrates. Nano Letters, 2010, 10, 47-51.	9.1	20
63	Surface-enhanced fluorescence from metal sculptured thin films with application to biosensing in water. Applied Physics Letters, 2009, 94, 063106.	3.3	65
64	Patterning concept for sculptured nanostructures with arbitrary periods. Applied Physics Letters, 2009, 95, 103107.	3.3	8
65	lon beam induced anisotropic deformation of Si nanosprings. Journal Physics D: Applied Physics, 2009, 42, 145404.	2.8	7
66	Large area metal dot matrices made by diffraction mask projection laser ablation. Physica Status Solidi - Rapid Research Letters, 2008, 2, 34-36.	2.4	14
67	Growth of Si nanorods in honeycomb and hexagonal-closed-packed arrays using glancing angle deposition. Journal of Applied Physics, 2008, 103, .	2.5	23
68	Glancing angle sputter deposited nanostructures on rotating substrates: Experiments and simulations. Journal of Applied Physics, 2008, 104, .	2.5	61
69	Temperature effect on the glancing angle deposition of Si sculptured thin films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2008, 26, 881-886.	2.1	31
70	Rapid thermal and swift heavy ion induced annealing of Co ion implanted GaN films. Journal of Applied Physics, 2008, 103, 124904.	2.5	6
71	Ordered silicon nanostructures by ion beam induced glancing angle deposition. Journal of Vacuum Science & Technology B, 2007, 25, 833.	1.3	27
72	Chiral silicon nanostructures. Nuclear Instruments & Methods in Physics Research B, 2006, 244, 40-44.	1.4	17

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73	A new mask blank deposition tool. Microelectronic Engineering, 2006, 83, 718-722.	2.4	1
74	Nanoscale laser patterning of thin gold films. Philosophical Magazine Letters, 2006, 86, 661-667.	1.2	11
75	Recrystallization behavior in chiral sculptured thin films from silicon. Journal of Applied Physics, 2006, 100, 016107.	2.5	17
76	Nanostructure fabrication by glancing angle ion beam assisted deposition of silicon. Applied Physics A: Materials Science and Processing, 2005, 81, 481-486.	2.3	29
77	Ion beam sputter deposition of soft x-ray Moâ^•Si multilayer mirrors. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 959.	1.6	13
78	Comparison of ion-beam-assisted molecular beam epitaxy with conventional molecular beam epitaxy of thin hexagonal gallium nitride films. Journal of Crystal Growth, 2004, 264, 184-191.	1.5	24
79	Semiconductor Nanowires Prepared by Diffraction-Mask-Projection Excimer-Laser Patterning. Nano Letters, 2004, 4, 895-897.	9.1	20